155Mbps/622Mbps/1.25Gbps/2.5Gbps

High Speed InGaAs Photodiodes

FCI-InGaAs-XXX series with active area sizes of 55µm, 70µm, 120µm, 300µm, 400µm and 500µm, exhibit the characteristics need for Datacom and Telecom applications. Low capacitance, low dark current and high responsivity from 1100nm to 1620nm make these devices ideal for high-bit rate receivers used in LAN, MAN, WAN, and other high speed communication systems. The photodiodes are packaged in 3 lead isolated TO-46 cans or in 1 pin pill packages with AR coated flat windows or micro lenses to enhance coupling efficiency. FCI-InGaAs-XXX series is also offered with FC, SC, ST and SMA receptacles.



APPLICATIONS

- High Speed Optical Communications
- Single/Multi-Mode Fiber Optic
 - •
- Gigabit Ethernet/Fibre Channel
- SONET/SDH, ATM

Receiver

Optical Taps

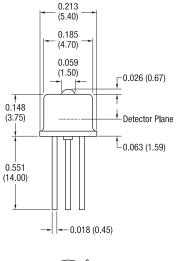
FEATURES

- High Speed
- High Responsivity
- Low Noise
- Spectral Range
 900nm to 1700nm

Absolute Maximum Ratings PARAMETERS SYMBOL MIN MAX UNITS $\mathsf{T}_{\mathsf{stg}}$ -55 +125 °C Storage Temperature Operating Temperature T_{op} -40 +75 °C Soldering Temperature +260 °C $\mathsf{T}_{\mathsf{sld}}$ ---

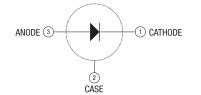
Electro-Optical Characteristics T _A =23°C															С						
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-55			FCI-InGaAs-70			FCI-InGaAs-120			FCI-InGaAs-300			FCI-InGaAs-400			FCI-InGaAs-500			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	ΤΥΡ	MAX	MIN	ТҮР	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Active Area Diameter	AA_{ϕ}			55			70			120			300			400			500		μm
Responsivity (Flat Window Package)	R _λ	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
		λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	Cj	V _R = 5.0V		1.0			1.5			2.0			10.0			14.0			20.0		pF
Dark Current	Id	V _R = 5.0V		0.02	2		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_{R} = 5.0V,$ $R_{L} = 50\Omega$ 10% to 90%			0.20			0.20			0.30			1.5			3.0			10.0	ns
Max. Revervse Voltage					20			20			20			15			15			15	V
Max. Reverse Current					0.5			1			2			2			2			2	mA
Max. Forward Current					5			5			5			8			8			8	mA
NEP				2.66E- 15			3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz

High Speed InGaAs Photodiodes

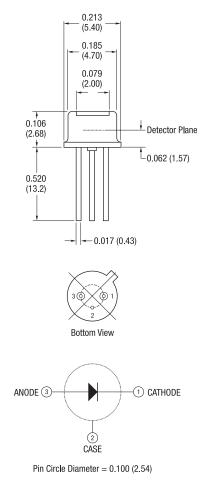


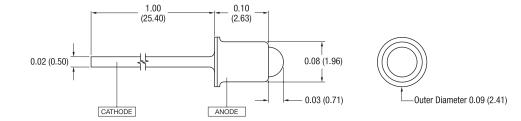






Pin Circle Diameter = 0.100 (2.54)





Notes:

- All units in inches (mm).
- All tolerances: 0.005 (0.125).
- Please specify when ordering the flat window or lens cap devices.
- The flat window devices have broadband AR
- coatings centered at 1310nm. • The thickness of the flat window=0.008 (0.21).
- The thickness of the flat window=0.008 (0.21)